

25 Spring ECEN 607: Advanced Analog Circuit Tech  
Design Pre-lab Report

Lab 2: Two-Stage Amplifier Design with  $3\sigma$  Driven  
Statistical Corner Extraction

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1. A PMOS input, two-stage Miller compensated op-amp is shown below. Obtain the expressions for
- From your background in ECEN-704/474, obtain the DC Gain ( $A_{v0}$ ), frequency of the dominant pole ( $p1$ ), Second pole ( $p2$ ), Zero ( $z$ ), Gain bandwidth product (GBW). Find the expression for Phase Margin (PM).

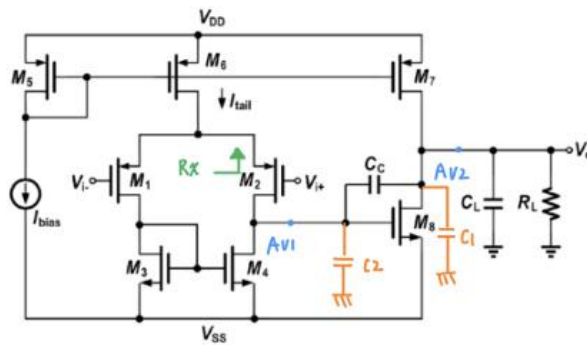


Figure 1: PMOS Two-Stage Miller Opamp

$$A_{v0} : \text{DC gain} = A_{v1} \times A_{v2} \quad R_X = g_{m2} r_{ds2} r_{ds6} + r_{ds2} + r_{ds6}$$

$$A_{v1} : -g_{m2} (R_X \parallel r_{ds4})$$

$$A_{v2} : -g_{m8} (r_{ds8} \parallel r_{ds7} \parallel R_L)$$

$$C_2 : (1 + A_{v2}) C_c \approx A_{v2} C_c$$

$$C_1 : (1 + \frac{1}{A_{v2}}) C_c \approx 0$$

$$\omega_{p1} : \frac{1}{(R_X \parallel r_{ds4})(A_{v2} C_c)} \quad (f = \frac{\omega}{2\pi})$$

$$\omega_{p2} \Big|_{\text{high f } C_c = 0} : \frac{1}{(\frac{1}{g_{m8}} \parallel r_{ds7} \parallel r_{ds8} \parallel R_L) C_L} \approx \frac{g_{m8}}{C_L}$$

$$\omega_Z : \frac{g_{m8}}{C_c}$$

$$W_{GBW} : \frac{g_{m2}}{C_c}$$

$$PM : 90^\circ - \tan^{-1} \left( \frac{W_{GBW}}{\omega_{p2}} \right) - \tan^{-1} \left( \frac{W_{GBW}}{\omega_Z} \right)$$

2. Select the current in different branches as well as dimensions of the transistors to satisfy the following specifications:

**Table 1:** Design specifications. Notice that VDD, VSS, CL and RL are given

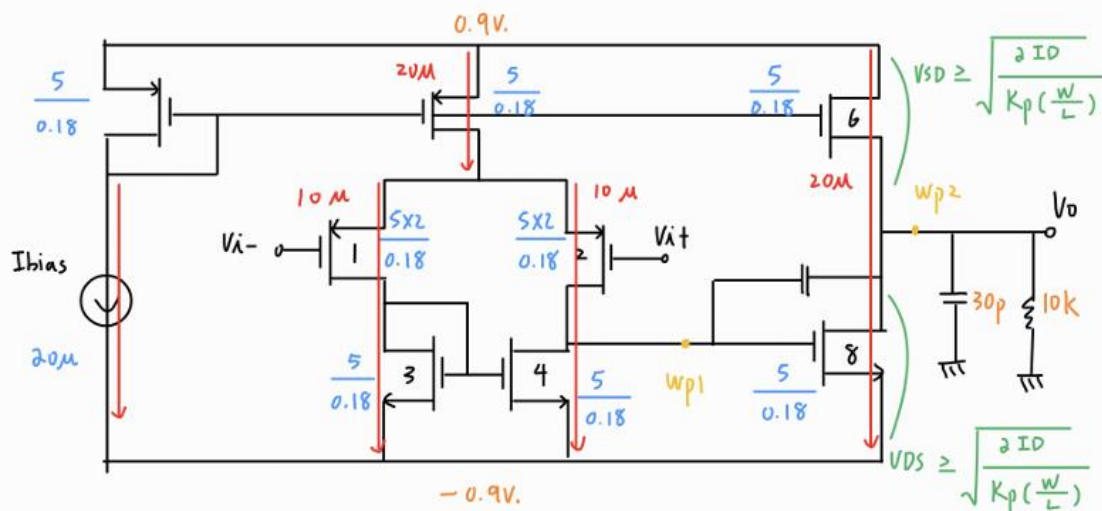
$V_{DD}$	0.9V
$V_{SS}$	-0.9V
$A_{v0}$	> 40 dB
GBW	> 2 MHz
PM	> 45°
Output Swing	> 1 V
$C_L$	30 pF
$R_L$	10kΩ

**Table 2:** Reference parameters of 1.8 V NMOS transistors..

Sl. No	W/L ( $\mu\text{m}/\mu\text{m}$ )	$V_{th}$ (mV)	$\mu n^*C_{ox}$ (mF/Vs)	$\theta$	$\lambda$ (mV <sup>-1</sup> )	$A_i$		$f_t$ (GHz)
						(V)	(dB)	
1	0.5/0.18	0.46	0.167	0.92	263	21.17	26.51	51.23
2	5/0.18	0.458	0.215	1.28	329.406	21.65	26.71	49.12
3	5/0.27	0.447	0.214	0.994	131.158	45.212	33.11	26.82

**Table 3:** Reference parameters of 1.8 V PMOS transistors

Sl. No	W/L ( $\mu\text{m}/\mu\text{m}$ )	$V_{tp}$ (mV)	$\mu p^*C_{ox}$ ( $\mu\text{F}/\text{Vs}$ )	$\theta$	$\lambda$ (mV <sup>-1</sup> )	$A_i$		$f_t$ (GHz)
						(V)	(dB)	
1	0.5/0.18	0.43	47.2	0.744	289.27	17.39	24.81	17.41
2	5/0.18	0.413	56.22	0.77	292.15	17.63	24.93	19.64
3	5/0.27	0.42	47.37	0.653	158.16	28.085	28.97	8.851



$$g_m = \sqrt{2 I_D \mu n c_{ox} \frac{W}{L}} \quad r_{ds} = \frac{1}{\lambda I_D}$$

$$160.882k$$

$$g_{m2} = 249.93\mu$$

$$r_{ds2} = 342.28k \quad r_{ds4} = 303.57k$$

$$A_{v1} = 40.20$$

$$g_{m8} = 488.76 \mu$$

$$r_{ds8} = 303.57k$$

$$r_{ds7} = 342.28k$$

$$R_L = 10k$$

$$A_{v2} = 4.88$$

$$A_{vo} = 196.176 = 45.85 \text{ dB}$$

$$GBW = \frac{g_{m2}}{2\pi \cdot C_c} \geq 2M \quad C_c \leq 19.89 \text{ pF}$$

$$C_c = 10 \text{ pF}$$

$$GBW = 3.97 M$$

$$f_{p1} = \frac{-1}{2\pi \times |A_{v2}| C_c \times 160.822k} = 20.289k \quad f_{p2} = \frac{-g_{m8}}{2\pi C_L} = 2.59 M \text{ Hz}$$

$$\omega_z = \frac{g_{m8}}{2\pi \times C_c} = 7.78 M \text{ Hz}$$

$$PM = 90^\circ - \tan^{-1} \frac{GBW}{\omega_{p2}} + \tan^{-1} \frac{GBW}{\omega_z} = 60.18^\circ$$

$56.89^\circ \qquad 27.07^\circ$

$$-0.9 + \sqrt{\frac{2 I_D}{K_N \left(\frac{W}{L}\right)}} \leq V_o \leq 0.9 - \sqrt{\frac{2 I_D}{K_P \left(\frac{W}{L}\right)}}$$

$0.08 \qquad 0.16$

$$-0.82 \leq V_o \leq 0.74$$

$$\text{Swing} : 1.56$$